**Abstract**

**Polishing pad and method for polishing a semiconductor wafer**

A method for polishing a semiconductor wafer, wherein, in a first step, the rear side of the semiconductor wafer is polished by means of a polishing pad comprising fixedly bonded abrasives having a grain size of 0.1-1.0 µm, and with the supply of a polishing agent which is free of solid materials and which has a pH value of at least 11.8, and, in a second step, the front side of the semiconductor wafer is polished, wherein a polishing agent having a pH value of less than 11.8 is supplied.

A polishing pad for use in apparatuses for polishing semiconductor wafer, comprising a layer containing abrasives, a layer composed of a stiff plastic and also a compliant, non-woven layer, wherein the layers are bonded to one another by means of pressure-sensitive adhesive layers.

No Figure.